

Figure 1 - Device cross section of optical gate (A) and Scaled Gamma Gate (B) MOSFETs with $L_{GD} = 11.5 \mu\text{m}$ (black), $6.5 \mu\text{m}$ (blue), $12.26 \mu\text{m}$ (gray) and $7.26 \mu\text{m}$ (red)

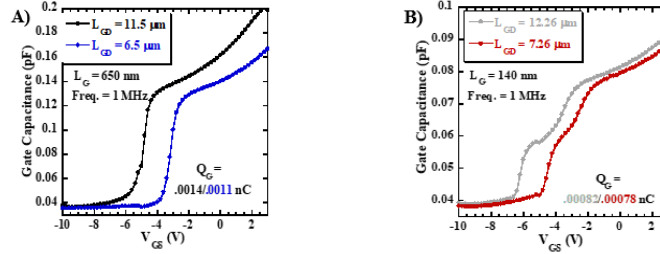


Figure 2 – Gate Capacitance (C_G) as a function of Gate-Source Voltage (V_{GS}) for optical gate (A) and Scaled Gamma Gate (B) MOSFETs with $L_{GD} = 11.5 \mu\text{m}$ (black), $6.5 \mu\text{m}$ (blue), $12.26 \mu\text{m}$ (gray) and $7.26 \mu\text{m}$ (red)

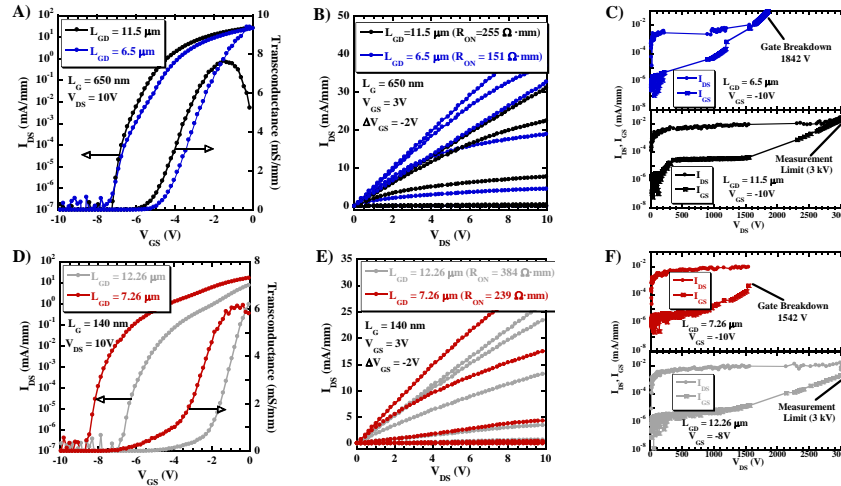


Figure 3 – Standard IV characteristics for optical gate (A-C) and Scaled Gamma Gate (D-F) MOSFETs with $L_{GD} = 11.5 \mu\text{m}$ (black), $6.5 \mu\text{m}$ (blue), $12.26 \mu\text{m}$ (gray) and $7.26 \mu\text{m}$ (red)

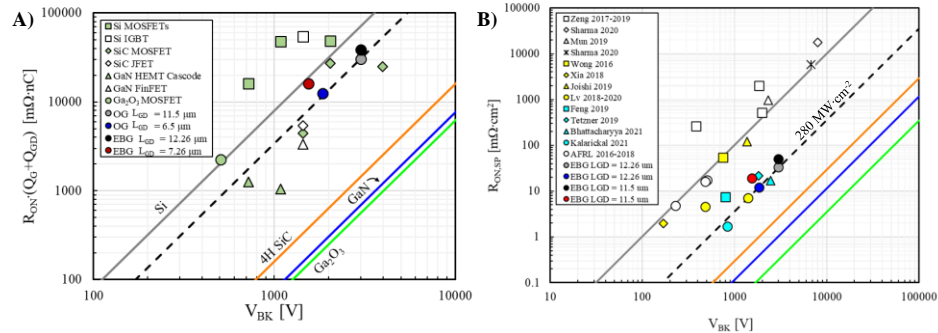


Figure 4 – $R_{ON}Q_G$ (A) and PFOM (B) benchmarking of these devices versus state of the art technology, assuming 3000 V breakdown